

**IN THE ABSTRACT**

Please amend the Abstract as set forth below in marked-up form.

A pair of reflective masks is provided in a photolithography process, wherein pattern forming elements are divided into respective [direction] directions relative to a projection vector of an EUV ray, so that each of the reflective masks has the same pattern forming elements extending in one direction. The exposure process is [sequentially] carried out sequentially to an object to be exposed using respective reflective [mask] masks, and when [the] a reflection mask is changed from one to the other, the object and the other reflective mask are rotated so that the angle of the object and the projection vector becomes the same angle with the reflective mask before it is changed.